



UT4422

Power MOSFET

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

DESCRIPTION

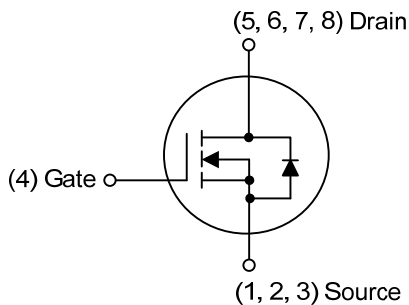
The UTC **UT4422** is a N-channel MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance and high switching speed.

The UTC **UT4422** is suitable for load switch and battery protection applications.

FEATURES

- * $R_{DS(ON)} \leq 8.5 \text{ m}\Omega @ V_{GS} = 10V, I_D = 8.0A$
- * $R_{DS(ON)} \leq 13 \text{ m}\Omega @ V_{GS} = 4.5V, I_D = 8.0A$
- * Low Capacitance
- * Low Gate Charge
- * Fast Switching Capability
- * Avalanche Energy Specified

SYMBOL

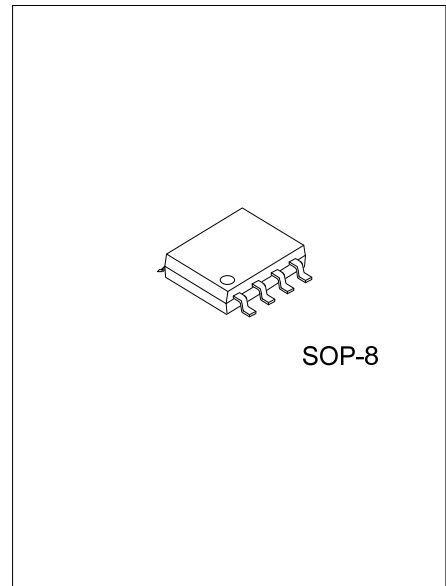


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing		
Lead Free	Halogen Free		1	2	3	4	5	6		7	8
UT4422L-S08-R	UT4422G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

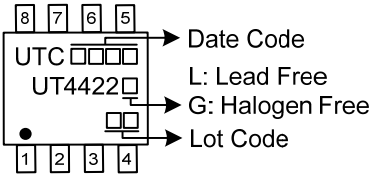
Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UT4422G-S08-R</p> <ul style="list-style-type: none"> (1) Packing Type (2) Package Type (3) Green Package 	<ul style="list-style-type: none"> (1) R: Tape Reel (2) S08: SOP-8 (3) G: Halogen Free and Lead Free, L: Lead Free
--	---



SOP-8

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage	V_{GSS}	± 20	V	
Continuous Drain Current (Note 1)	I_D	11	A	
Pulsed Drain Current	I_{DM}	50	A	
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	12	mJ
Power Dissipation	P_D	2	W	
Junction Temperature	T_J	+150	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 0.1\text{mH}$, $I_{AS} = 15.7\text{A}$, $V_{DD} = 20\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	90	$^\circ\text{C/W}$
Junction to Case	θ_{JC}	62.5 (Note)	$^\circ\text{C/W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

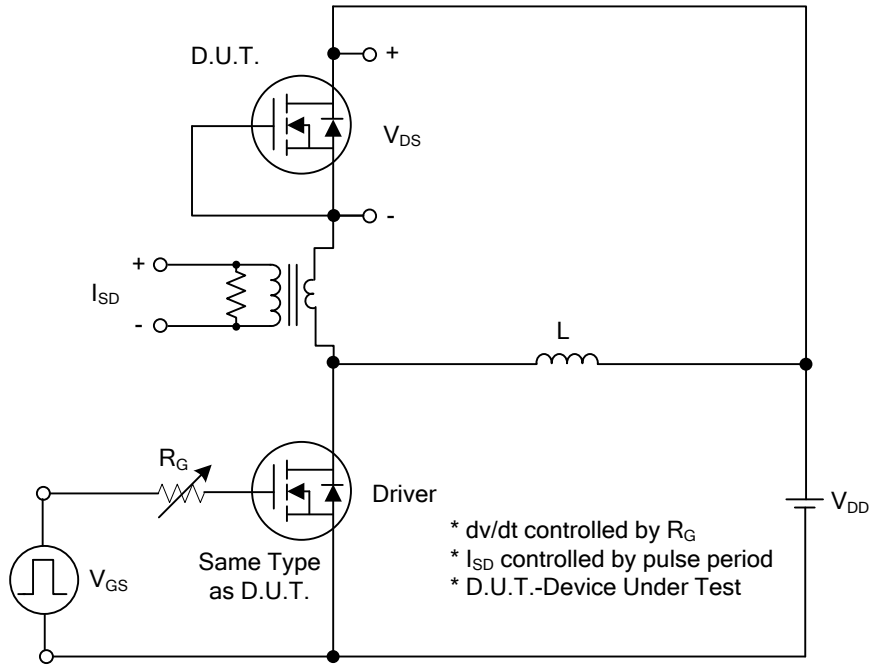
■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	30			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.0		3.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=8.0\text{A}$			8.5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=8.0\text{A}$			13	$\text{m}\Omega$
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS}=15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$		1000		pF
Output Capacitance	C_{OSS}			320		pF
Reverse Transfer Capacitance	C_{RSS}			180		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=15\text{V}$, $V_{GS}=10\text{V}$, $I_D=11\text{A}$		38		nC
Gate Source Charge	Q_{GS}			4		nC
Gate Drain Charge	Q_{GD}			12		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DS}=15\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=11\text{A}$, $R_G=3.0\Omega$ (Note 1, 2)		10		ns
Turn-ON Rise Time	t_R			17		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			25		ns
Turn-OFF Fall-Time	t_F			22		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S					A
Maximum Body-Diode Pulsed Current	I_{SM}					A
Diode Forward Voltage	V_{SD}	$I_S=11\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$I_S=11\text{A}$, $V_{GS}=0\text{V}$		260		ns
Reverse Recovery Charge	Q_{rr}	$dI_F/dt=100\text{A}/\mu\text{s}$ (Note1)		1.2		μC

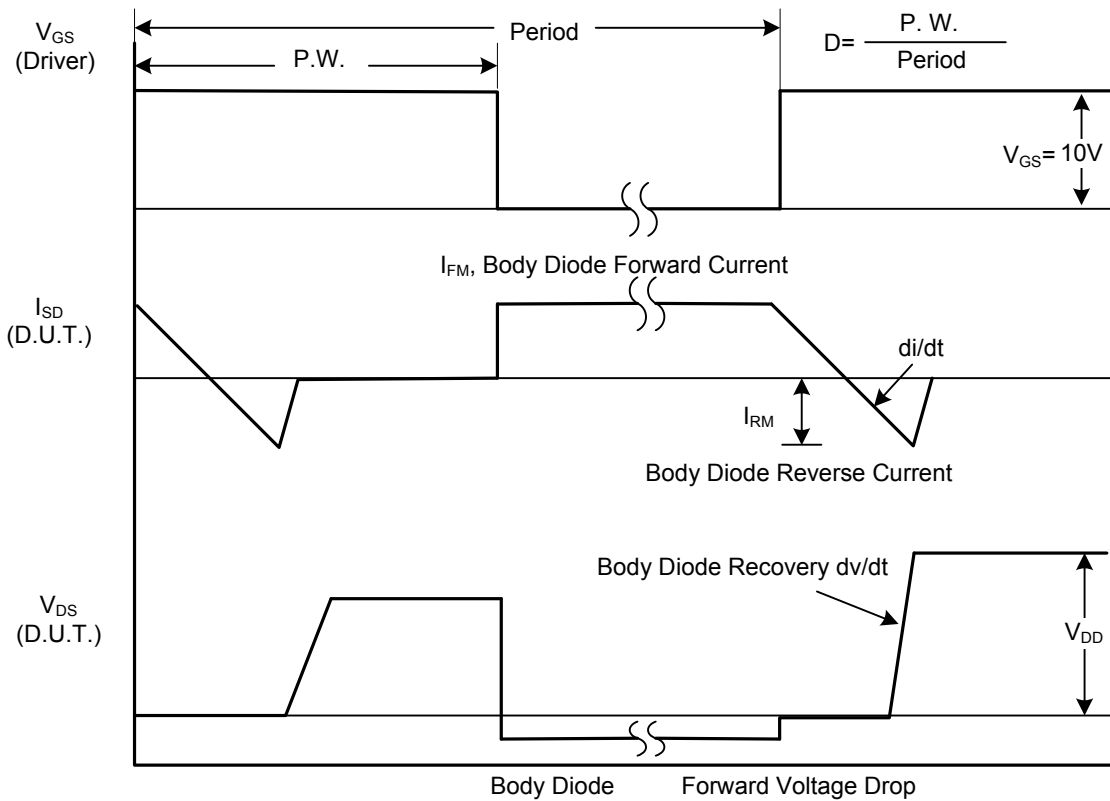
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

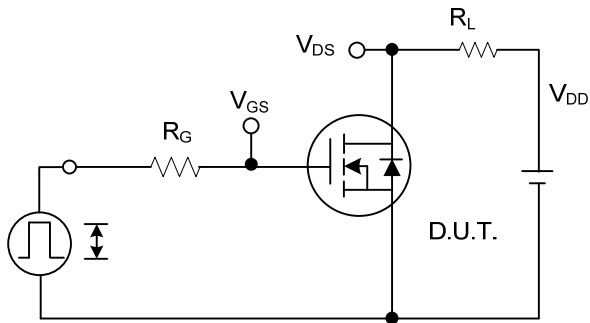


Peak Diode Recovery dv/dt Test Circuit

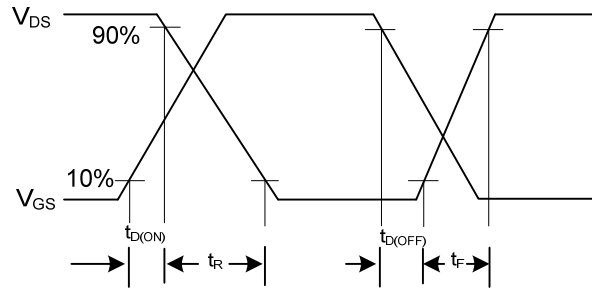


Peak Diode Recovery dv/dt Waveforms

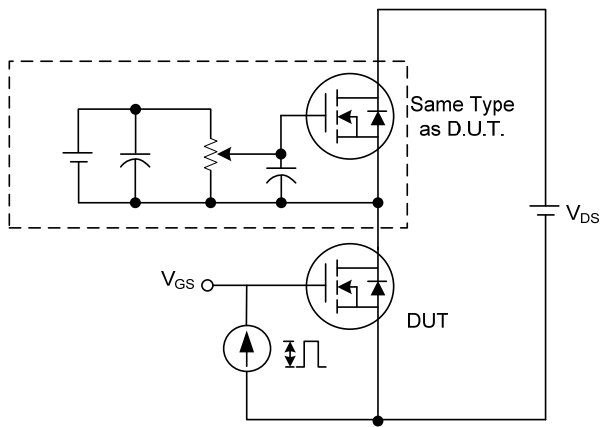
■ TEST CIRCUITS AND WAVEFORMS



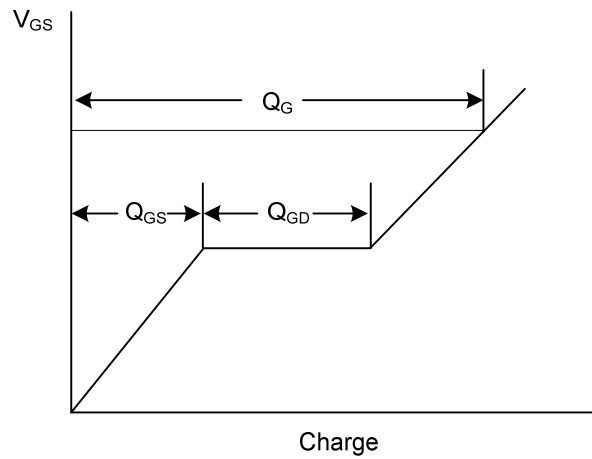
Switching Test Circuit



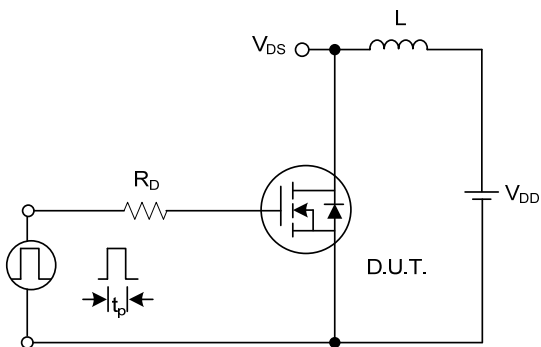
Switching Waveforms



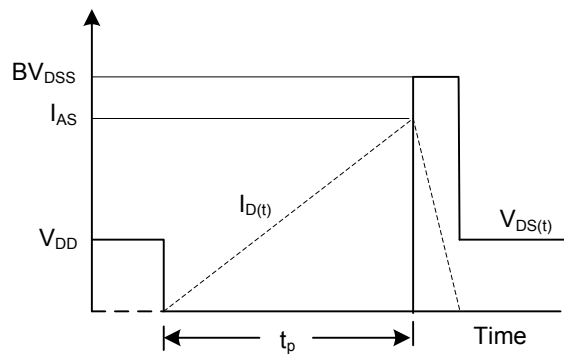
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.